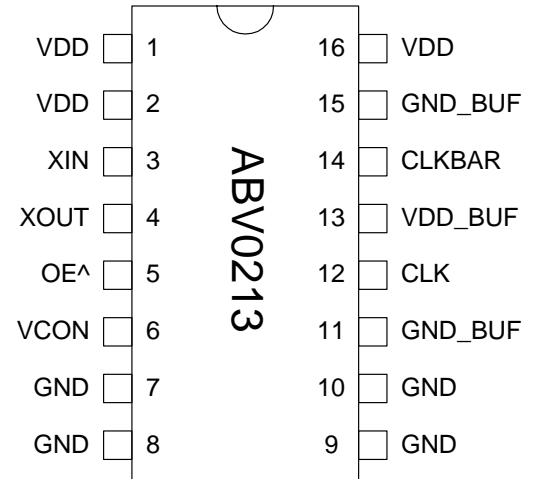


192MHz – 400MHz Low Phase Noise PECL VCXO (12 – 25MHz Crystal)

FEATURES

- Low phase noise output for the 192MHz to 400MHz range (-134 dBc at 10kHz offset).
- PECL output.
- 12 to 25MHz crystal input.
- Integrated crystal load capacitor: no external load capacitor required.
- Output Enable selector.
- 3.3V operation.
- Available in 16 Pin TSSOP.

PIN CONFIGURATION



Note: ^ denotes internal pull up

$$F_{OUT} = F_{XIN} \times 16$$

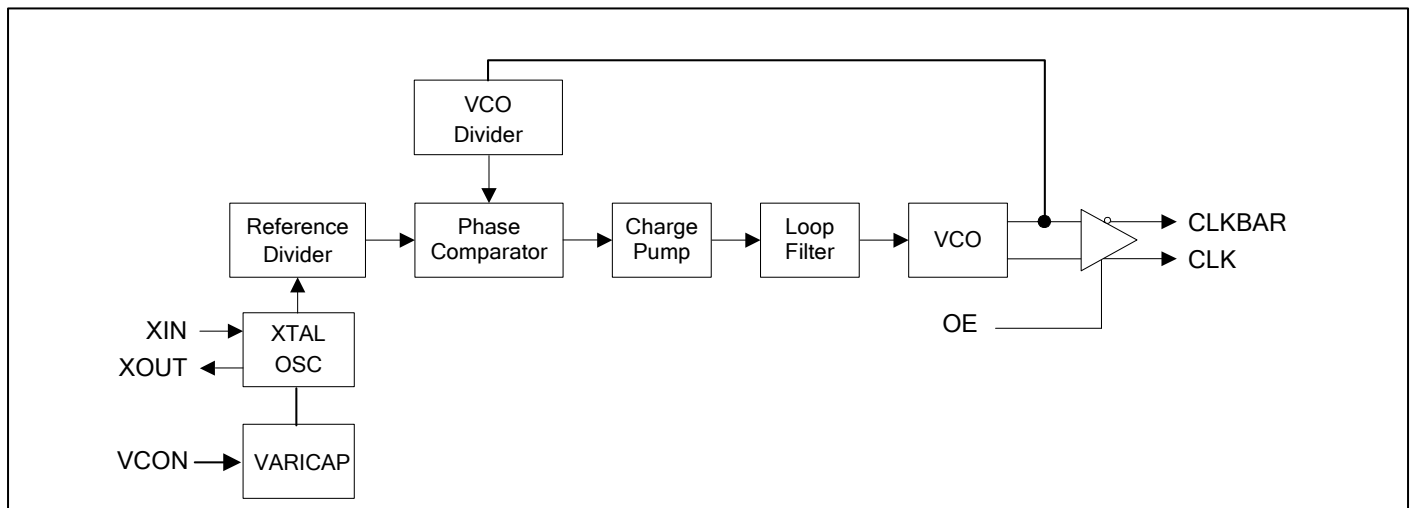
DESCRIPTION

The ABV0213 is a monolithic low jitter and low phase noise (-134dBc/Hz @ 10kHz offset) VCXO IC with PECL output, for 192MHz to 400MHz output range. It provides a low phase noise reference frequency using a low cost crystal.

The chip delivers an output frequency of $F_{XIN} \times 16$. This makes the ABV0213 ideal for a wide range of applications.

| OE (Pin 5) | Output State |
|-------------|----------------|
| 0 | Tri-state |
| 1 (Default) | Output enabled |

BLOCK DIAGRAM



192MHz – 400MHz Low Phase Noise PECL VCXO (12 – 25MHz Crystal)

PIN DESCRIPTIONS

| Name | Number | Type | Description |
|---------|----------|------|---|
| VDD | 1,2,16 | P | Power supply. |
| XIN | 3 | I | Crystal input. See Crystal Specifications on page 2. |
| XOUT | 4 | I | Crystal output. See Crystal Specifications on page 2. |
| OE | 5 | I | Output enable input. Disables (tri-state) output when low. Internal pull-up enables output by default if pin is not connected to low. |
| VCON | 6 | - | Voltage Control input. |
| GND | 7,8,9,10 | P | Ground. |
| GND_BUF | 11,15 | P | Ground for output buffers. |
| CLK | 12 | O | True clock output. |
| VDD_BUF | 13 | P | Power supply for output buffers. |
| CLKB | 14 | O | Complementary clock output. |

ELECTRICAL SPECIFICATIONS

1. Absolute Maximum Ratings

| PARAMETERS | SYMBOL | MIN. | MAX. | UNITS |
|-----------------------------------|----------|------|--------------|-------|
| Supply Voltage | V_{DD} | | 4.6 | V |
| Input Voltage, dc | V_I | -0.5 | $V_{DD}+0.5$ | V |
| Output Voltage, dc | V_O | -0.5 | $V_{DD}+0.5$ | V |
| Storage Temperature | T_S | -65 | 150 | °C |
| Ambient Operating Temperature* | T_A | -40 | 85 | °C |
| Junction Temperature | T_J | | 125 | °C |
| Lead Temperature (soldering, 10s) | | | 260 | °C |
| ESD Protection, Human Body Model | | | 2 | kV |

Exposure of the device under conditions beyond the limits specified by Maximum Ratings for extended periods may cause permanent damage to the device and affect product reliability. These conditions represent a stress rating only, and functional operations of the device at these or any other conditions above the operational limits noted in this specification is not implied.

* Note: Operating Temperature is guaranteed by design for all parts (COMMERCIAL and INDUSTRIAL), but tested for COMMERCIAL grade only.

2. Crystal Specifications

| PARAMETERS | SYMBOL | CONDITIONS | MIN. | TYP. | MAX. | UNITS |
|-----------------------------|------------------|---------------------------|------|------|------|----------|
| Crystal Resonator Frequency | F_{XIN} | Parallel Fundamental Mode | 12 | | 25 | MHz |
| Crystal Loading Rating | $C_L (xtal)$ | At VCON = 1.65V | | 9.5 | | pF |
| Crystal Pullability | $C_0/C_1 (xtal)$ | AT cut | | | 250 | - |
| Recommended ESR | R_E | AT cut | | | 30 | Ω |

192MHz – 400MHz Low Phase Noise PECL VCXO (12 – 25MHz Crystal)

3. General Electrical Specifications

| PARAMETERS | SYMBOL | CONDITIONS | MIN. | TYP. | MAX. | UNITS |
|---|-----------------|---------------------------------|------|------|------|-------|
| Supply Current, Dynamic (with Loaded Outputs) | I _{DD} | PECL | | | 80 | mA |
| Operating Voltage | V _{DD} | | 2.97 | | 3.63 | V |
| Output Clock Duty Cycle | | @ V _{DD} – 1.3V (PECL) | 45 | 50 | 55 | % |
| Short Circuit Current | | | | ±50 | | mA |

4. Jitter and Phase Noise Specification

| PARAMETERS | CONDITIONS | MIN. | TYP. | MAX. | UNITS |
|---------------------------------|---|------|------|------|--------|
| Period jitter RMS | With capacitive decoupling between VDD and GND. | | 5 | | ps |
| Accumulated jitter RMS | With capacitive decoupling between VDD and GND. Over 10,000 cycles. | | 11 | | ps |
| Phase Noise relative to carrier | 311MHz @100Hz offset | | -90 | | dBc/Hz |
| Phase Noise relative to carrier | 311MHz @1kHz offset | | -115 | | dBc/Hz |
| Phase Noise relative to carrier | 311MHz @10kHz offset | | -125 | | dBc/Hz |
| Phase Noise relative to carrier | 311MHz @100kHz offset | | -119 | | dBc/Hz |

5. Voltage Control Crystal Oscillator

| PARAMETERS | SYMBOL | CONDITIONS | MIN. | TYP. | MAX. | UNITS |
|----------------------------|----------------------|---|------|------|------|-------|
| VCXO Stabilization Time * | T _{VCXOSTB} | From power valid | | | 10 | ms |
| VCXO Tuning Range | | F _{XIN} = 12 – 25MHz; XTAL C ₀ /C ₁ < 250 0V ≤ VCON ≤ 3.3V | | 500 | | ppm |
| CLK output pullability | | VCON=1.65V, ±1.65V | ±200 | | | ppm |
| VCXO Tuning Characteristic | | | | 150 | | ppm/V |
| Pull range linearity | | | | | 10 | % |
| VCON pin input impedance | | | 2000 | | | kΩ |
| VCON modulation BW | | 0V ≤ VCON ≤ 3.3V, -3dB | 25 | | | kHz |

Note: Parameters denoted with an asterisk (*) represent nominal characterization data and are not production tested to any specific limits.

192MHz – 400MHz Low Phase Noise PECL VCXO (12 – 25MHz Crystal)

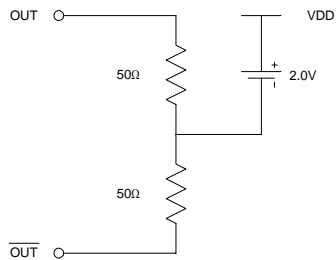
6. PECL Electrical Characteristics

| PARAMETERS | SYMBOL | CONDITIONS | MIN. | MAX. | UNITS |
|---------------------|----------|--|------------------|------------------|-------|
| Output High Voltage | V_{OH} | $R_L = 50 \Omega$ to $(V_{DD} - 2V)$ (see figure) | $V_{DD} - 1.025$ | | V |
| Output Low Voltage | V_{OL} | | | $V_{DD} - 1.620$ | V |

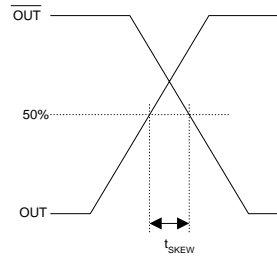
7. PECL Switching Characteristics

| PARAMETERS | SYMBOL | CONDITIONS | MIN. | TYP. | MAX. | UNITS |
|-----------------|--------|----------------|------|------|------|-------|
| Clock Rise Time | t_r | @20/80% - PECL | | 0.6 | 1.5 | ns |
| Clock Fall Time | t_f | @80/20% - PECL | | 0.5 | 1.5 | ns |

PECL Levels Test Circuit



PECL Output Skew



PECL Transition Time Waveform

